

IN THE SPECIFICATION

Please amend the following paragraph starting on Page 3, line 7 as follows:

US6344662 describes the creation of a TFT having a hybrid organic-inorganic semiconductor layer. The gate metallization is formed using electron beam evaporation and the metal source and drain are formed separately by vapor deposition. Claim 6 states, without further explanation or clarification, that the gate electrode is produced by a process selected from the group consisting of evaporation, sputtering, chemical vapor deposition, electrodeposition, spin coating, and electroless plating.